

## Preliminary datasheet

### EconoPIM™2 module with TRENCHSTOP™ IGBT7 and Emitter Controlled 7 diode and PressFIT / NTC

#### Features

- Electrical features
  - $V_{CES} = 1200\text{ V}$
  - $I_{C\text{ nom}} = 35\text{ A} / I_{CRM} = 70\text{ A}$
  - TRENCHSTOP™ IGBT7
  - Low  $V_{CESat}$
  - Overload operation up to  $175^{\circ}\text{C}$
- Mechanical features
  - High power and thermal cycling capability
  - Integrated NTC temperature sensor
  - Copper base plate
  - $\text{Al}_2\text{O}_3$  substrate with low thermal resistance
  - PressFIT contact technology



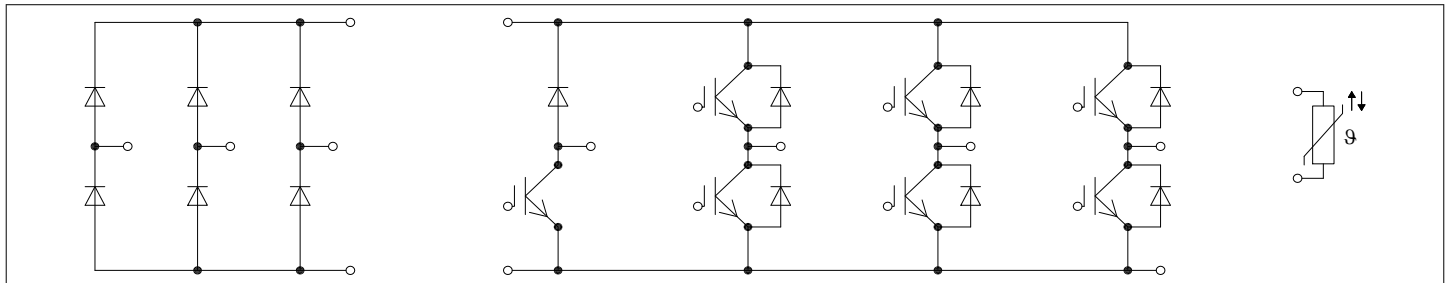
#### Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

#### Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

#### Description



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**1 Package**

## 1 Package

**Table 1** Insulation coordination

| Parameter                    | Symbol      | Note or test condition                         | Values    | Unit |
|------------------------------|-------------|------------------------------------------------|-----------|------|
| Isolation test voltage       | $V_{ISOL}$  | RMS, $f = 50 \text{ Hz}$ , $t = 1 \text{ min}$ | 2.5       | kV   |
| Material of module baseplate |             |                                                | Cu        |      |
| Internal Isolation           |             | basic insulation (class 1, IEC 61140)          | $Al_2O_3$ |      |
| Creepage distance            | $d_{Creep}$ | terminal to heatsink                           | 10.0      | mm   |
| Clearance                    | $d_{Clear}$ | terminal to heatsink                           | 7.5       | mm   |
| Comparative tracking index   | $CTI$       |                                                | > 200     |      |
| RTI Elec.                    | $RTI$       | housing                                        | 140       | °C   |

**Table 2** Characteristic values

| Parameter                                | Symbol        | Note or test condition                         | Values    |      |      | Unit |
|------------------------------------------|---------------|------------------------------------------------|-----------|------|------|------|
|                                          |               |                                                | Min.      | Typ. | Max. |      |
| Stray inductance module                  | $L_{SCE}$     |                                                |           | 35   |      | nH   |
| Module lead resistance, terminals - chip | $R_{AA'+CC'}$ | $T_C = 25^\circ\text{C}$ , per switch          |           | 6.9  |      | mΩ   |
| Module lead resistance, terminals - chip | $R_{CC'+EE'}$ | $T_C = 25^\circ\text{C}$ , per switch          |           | 5.9  |      | mΩ   |
| Storage temperature                      | $T_{stg}$     |                                                | -40       |      | 125  | °C   |
| Mounting torque for modul mounting       | $M$           | - Mounting according to valid application note | M5, Screw | 3    | 6    | Nm   |
| Weight                                   | $G$           |                                                |           | 180  |      | g    |

## 2 IGBT, Inverter

**Table 3** Maximum rated values

| Parameter                         | Symbol    | Note or test condition            |                             | Values | Unit |
|-----------------------------------|-----------|-----------------------------------|-----------------------------|--------|------|
| Collector-emitter voltage         | $V_{CES}$ |                                   | $T_{vj} = 25^\circ\text{C}$ | 1200   | V    |
| Continuous DC collector current   | $I_{CDC}$ | $T_{vj \max} = 175^\circ\text{C}$ | $T_C = 105^\circ\text{C}$   | 35     | A    |
| Repetitive peak collector current | $I_{CRM}$ | $t_P = 1 \text{ ms}$              |                             | 70     | A    |
| Gate-emitter peak voltage         | $V_{GES}$ |                                   |                             | ±20    | V    |

**Table 4**                      **Characteristic values**

| Parameter                            | Symbol        | Note or test condition                                                                                                                        |                                             | Values |       |       | Unit     |
|--------------------------------------|---------------|-----------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------|--------|-------|-------|----------|
|                                      |               |                                                                                                                                               |                                             | Min.   | Typ.  | Max.  |          |
| Collector-emitter saturation voltage | $V_{CE\ sat}$ | $I_C = 35\ A, V_{GE} = 15\ V$                                                                                                                 | $T_{vj} = 25\ ^\circ C$                     |        | 1.60  | TBD   | V        |
|                                      |               |                                                                                                                                               | $T_{vj} = 125\ ^\circ C$                    |        | 1.74  |       |          |
|                                      |               |                                                                                                                                               | $T_{vj} = 175\ ^\circ C$                    |        | 1.82  |       |          |
| Gate threshold voltage               | $V_{GEth}$    | $I_C = 0.75\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$                                                                                      |                                             | 5.15   | 5.80  | 6.45  | V        |
| Gate charge                          | $Q_G$         | $V_{GE} = \pm 15\ V, V_{CE} = 600\ V$                                                                                                         |                                             |        | 0.548 |       | $\mu C$  |
| Internal gate resistor               | $R_{Gint}$    | $T_{vj} = 25\ ^\circ C$                                                                                                                       |                                             |        | 0     |       | $\Omega$ |
| Input capacitance                    | $C_{ies}$     | $f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$                                                                          |                                             |        | 6.62  |       | nF       |
| Reverse transfer capacitance         | $C_{res}$     | $f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$                                                                          |                                             |        | 0.023 |       | nF       |
| Collector-emitter cut-off current    | $I_{CES}$     | $V_{CE} = 1200\ V, V_{GE} = 0\ V$                                                                                                             | $T_{vj} = 25\ ^\circ C$                     |        |       | 0.007 | mA       |
| Gate-emitter leakage current         | $I_{GES}$     | $V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$                                                                                        |                                             |        |       | 100   | nA       |
| Turn-on delay time (inductive load)  | $t_{don}$     | $I_C = 35\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega$                                                                     | $T_{vj} = 25\ ^\circ C$                     |        | 0.051 |       | $\mu s$  |
|                                      |               |                                                                                                                                               | $T_{vj} = 125\ ^\circ C$                    |        | 0.052 |       |          |
|                                      |               |                                                                                                                                               | $T_{vj} = 175\ ^\circ C$                    |        | 0.053 |       |          |
| Rise time (inductive load)           | $t_r$         | $I_C = 35\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega$                                                                     | $T_{vj} = 25\ ^\circ C$                     |        | 0.037 |       | $\mu s$  |
|                                      |               |                                                                                                                                               | $T_{vj} = 125\ ^\circ C$                    |        | 0.040 |       |          |
|                                      |               |                                                                                                                                               | $T_{vj} = 175\ ^\circ C$                    |        | 0.042 |       |          |
| Turn-off delay time (inductive load) | $t_{doff}$    | $I_C = 35\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$                                                                    | $T_{vj} = 25\ ^\circ C$                     |        | 0.250 |       | $\mu s$  |
|                                      |               |                                                                                                                                               | $T_{vj} = 125\ ^\circ C$                    |        | 0.330 |       |          |
|                                      |               |                                                                                                                                               | $T_{vj} = 175\ ^\circ C$                    |        | 0.350 |       |          |
| Fall time (inductive load)           | $t_f$         | $I_C = 35\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$                                                                    | $T_{vj} = 25\ ^\circ C$                     |        | 0.120 |       | $\mu s$  |
|                                      |               |                                                                                                                                               | $T_{vj} = 125\ ^\circ C$                    |        | 0.220 |       |          |
|                                      |               |                                                                                                                                               | $T_{vj} = 175\ ^\circ C$                    |        | 0.290 |       |          |
| Turn-on energy loss per pulse        | $E_{on}$      | $I_C = 35\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega, di/dt = 725\ A/\mu s (T_{vj} = 175\ ^\circ C)$   | $T_{vj} = 25\ ^\circ C$                     |        | 2.9   |       | mJ       |
|                                      |               |                                                                                                                                               | $T_{vj} = 125\ ^\circ C$                    |        | 4     |       |          |
|                                      |               |                                                                                                                                               | $T_{vj} = 175\ ^\circ C$                    |        | 4.66  |       |          |
| Turn-off energy loss per pulse       | $E_{off}$     | $I_C = 35\ A, V_{CE} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega, dv/dt = 3150\ V/\mu s (T_{vj} = 175\ ^\circ C)$ | $T_{vj} = 25\ ^\circ C$                     |        | 2.22  |       | mJ       |
|                                      |               |                                                                                                                                               | $T_{vj} = 125\ ^\circ C$                    |        | 3.58  |       |          |
|                                      |               |                                                                                                                                               | $T_{vj} = 175\ ^\circ C$                    |        | 4.4   |       |          |
| SC data                              | $I_{SC}$      | $V_{GE} \leq 15\ V, V_{CC} = 800\ V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$                                                               | $t_P \leq 8\ \mu s, T_{vj} = 150\ ^\circ C$ |        | 110   |       | A        |
|                                      |               |                                                                                                                                               | $t_P \leq 7\ \mu s, T_{vj} = 175\ ^\circ C$ |        | 100   |       |          |

**3 Diode, Inverter**

**Table 4 Characteristic values (continued)**

| Parameter                              | Symbol             | Note or test condition                                   | Values |       |       | Unit |
|----------------------------------------|--------------------|----------------------------------------------------------|--------|-------|-------|------|
|                                        |                    |                                                          | Min.   | Typ.  | Max.  |      |
| Thermal resistance, junction to case   | $R_{thJC}$         | per IGBT                                                 |        |       | 0.802 | K/W  |
| Thermal resistance, case to heatsink   | $R_{thCH}$         | per IGBT, $\lambda_{grease} = 1 \text{ W/(m}^2\text{K)}$ |        | 0.157 |       | K/W  |
| Temperature under switching conditions | $T_{vj\text{ op}}$ |                                                          | -40    |       | 175   | °C   |

Note:  $T_{vj\text{ op}} > 150^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

### 3 Diode, Inverter

**Table 5 Maximum rated values**

| Parameter                       | Symbol    | Note or test condition                   |                              | Values | Unit                 |
|---------------------------------|-----------|------------------------------------------|------------------------------|--------|----------------------|
| Repetitive peak reverse voltage | $V_{RRM}$ |                                          | $T_{vj} = 25^\circ\text{C}$  | 1200   | V                    |
| Continuous DC forward current   | $I_F$     |                                          |                              | 35     | A                    |
| Repetitive peak forward current | $I_{FRM}$ | $t_P = 1 \text{ ms}$                     |                              | 70     | A                    |
| $I^2t$ - value                  | $I^2t$    | $t_P = 10 \text{ ms}, V_R = 0 \text{ V}$ | $T_{vj} = 125^\circ\text{C}$ | 210    | $\text{A}^2\text{s}$ |
|                                 |           |                                          | $T_{vj} = 175^\circ\text{C}$ | 200    |                      |

**Table 6 Characteristic values**

| Parameter                     | Symbol   | Note or test condition                                                                                                               | Values                       |      |      | Unit          |
|-------------------------------|----------|--------------------------------------------------------------------------------------------------------------------------------------|------------------------------|------|------|---------------|
|                               |          |                                                                                                                                      | Min.                         | Typ. | Max. |               |
| Forward voltage               | $V_F$    | $I_F = 35 \text{ A}, V_{GE} = 0 \text{ V}$                                                                                           | $T_{vj} = 25^\circ\text{C}$  |      | 1.72 | TBD           |
|                               |          |                                                                                                                                      | $T_{vj} = 125^\circ\text{C}$ |      | 1.59 |               |
|                               |          |                                                                                                                                      | $T_{vj} = 175^\circ\text{C}$ |      | 1.52 |               |
| Peak reverse recovery current | $I_{RM}$ | $V_R = 600 \text{ V}, I_F = 35 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 725 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$ | $T_{vj} = 25^\circ\text{C}$  |      | 21   | A             |
|                               |          |                                                                                                                                      | $T_{vj} = 125^\circ\text{C}$ |      | 27   |               |
|                               |          |                                                                                                                                      | $T_{vj} = 175^\circ\text{C}$ |      | 31   |               |
| Recovered charge              | $Q_r$    | $V_R = 600 \text{ V}, I_F = 35 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 725 \text{ A}/\mu\text{s} (T_{vj} = 175^\circ\text{C})$ | $T_{vj} = 25^\circ\text{C}$  |      | 2.77 | $\mu\text{C}$ |
|                               |          |                                                                                                                                      | $T_{vj} = 125^\circ\text{C}$ |      | 4.93 |               |
|                               |          |                                                                                                                                      | $T_{vj} = 175^\circ\text{C}$ |      | 6.66 |               |

**Table 6** Characteristic values (continued)

| Parameter                              | Symbol             | Note or test condition                                                                                                                       | Values                   |       |      | Unit |
|----------------------------------------|--------------------|----------------------------------------------------------------------------------------------------------------------------------------------|--------------------------|-------|------|------|
|                                        |                    |                                                                                                                                              | Min.                     | Typ.  | Max. |      |
| Reverse recovery energy                | $E_{rec}$          | $V_R = 600\text{ V}$ , $I_F = 35\text{ A}$ ,<br>$V_{GE} = -15\text{ V}$ , $-di_F/dt = 725\text{ A}/\mu\text{s}$ ( $T_{vj} = 175\text{ °C}$ ) | $T_{vj} = 25\text{ °C}$  | 1.04  |      | mJ   |
|                                        |                    |                                                                                                                                              | $T_{vj} = 125\text{ °C}$ | 1.81  |      |      |
|                                        |                    |                                                                                                                                              | $T_{vj} = 175\text{ °C}$ | 2.47  |      |      |
| Thermal resistance, junction to case   | $R_{thJC}$         | per diode                                                                                                                                    |                          |       | 1.10 | K/W  |
| Thermal resistance, case to heatsink   | $R_{thCH}$         | per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$                                                                              |                          | 0.176 |      | K/W  |
| Temperature under switching conditions | $T_{vj\text{ op}}$ |                                                                                                                                              | -40                      |       | 175  | °C   |

Note:  $T_{vj\text{ op}} > 150\text{ °C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 4 Diode, Rectifier

**Table 7** Maximum rated values

| Parameter                               | Symbol      | Note or test condition  |                          | Values | Unit                 |
|-----------------------------------------|-------------|-------------------------|--------------------------|--------|----------------------|
| Repetitive peak reverse voltage         | $V_{RRM}$   | $T_{vj} = 25\text{ °C}$ |                          | 1600   | V                    |
| Maximum RMS forward current per chip    | $I_{FRMSM}$ | $T_C = 80\text{ °C}$    |                          | 70     | A                    |
| Maximum RMS current at rectifier output | $I_{RMSM}$  | $T_C = 80\text{ °C}$    |                          | 100    | A                    |
| Surge forward current                   | $I_{FSM}$   | $t_p = 10\text{ ms}$    | $T_{vj} = 25\text{ °C}$  | 560    | A                    |
|                                         |             |                         | $T_{vj} = 150\text{ °C}$ | 435    |                      |
| $I^2t$ - value                          | $I^2t$      | $t_p = 10\text{ ms}$    | $T_{vj} = 25\text{ °C}$  | 1570   | $\text{A}^2\text{s}$ |
|                                         |             |                         | $T_{vj} = 150\text{ °C}$ | 945    |                      |

**Table 8** Characteristic values

| Parameter                            | Symbol     | Note or test condition                                          | Values |       |       | Unit |
|--------------------------------------|------------|-----------------------------------------------------------------|--------|-------|-------|------|
|                                      |            |                                                                 | Min.   | Typ.  | Max.  |      |
| Forward voltage                      | $V_F$      | $I_F = 35\text{ A}$ , $T_{vj} = 150\text{ °C}$                  |        | 0.95  |       | V    |
| Reverse current                      | $I_r$      | $T_{vj} = 150\text{ °C}$ , $V_R = 1600\text{ V}$                |        | 1     |       | mA   |
| Thermal resistance, junction to case | $R_{thJC}$ | per diode                                                       |        |       | 0.870 | K/W  |
| Thermal resistance, case to heatsink | $R_{thCH}$ | per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$ |        | 0.171 |       | K/W  |

**Table 8** Characteristic values (continued)

| Parameter                              | Symbol       | Note or test condition | Values |      |      | Unit |
|----------------------------------------|--------------|------------------------|--------|------|------|------|
|                                        |              |                        | Min.   | Typ. | Max. |      |
| Temperature under switching conditions | $T_{vj, op}$ |                        | -40    |      | 150  | °C   |

## 5 IGBT-Chopper

**Table 9** Maximum rated values

| Parameter                         | Symbol    | Note or test condition        |                         | Values | Unit |
|-----------------------------------|-----------|-------------------------------|-------------------------|--------|------|
| Collector-emitter voltage         | $V_{CES}$ |                               | $T_{vj} = 25\text{ °C}$ | 1200   | V    |
| Continuous DC collector current   | $I_{CDC}$ | $T_{vj\ max} = 175\text{ °C}$ | $T_C = 115\text{ °C}$   | 25     | A    |
| Repetitive peak collector current | $I_{CRM}$ | $t_P = 1\text{ ms}$           |                         | 50     | A    |
| Gate-emitter peak voltage         | $V_{GES}$ |                               |                         | ±20    | V    |

**Table 10** Characteristic values

| Parameter                            | Symbol        | Note or test condition                                                                       |                          | Values |       |       | Unit |
|--------------------------------------|---------------|----------------------------------------------------------------------------------------------|--------------------------|--------|-------|-------|------|
|                                      |               |                                                                                              |                          | Min.   | Typ.  | Max.  |      |
| Collector-emitter saturation voltage | $V_{CE\ sat}$ | $I_C = 25\text{ A}, V_{GE} = 15\text{ V}$                                                    | $T_{vj} = 25\text{ °C}$  |        | 1.60  | TBD   | V    |
|                                      |               |                                                                                              | $T_{vj} = 125\text{ °C}$ |        | 1.74  |       |      |
|                                      |               |                                                                                              | $T_{vj} = 175\text{ °C}$ |        | 1.82  |       |      |
| Gate threshold voltage               | $V_{GEth}$    | $I_C = 0.525\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25\text{ °C}$                              |                          | 5.15   | 5.80  | 6.45  | V    |
| Gate charge                          | $Q_G$         | $V_{GE} = \pm 15\text{ V}, V_{CE} = 600\text{ V}$                                            |                          |        | 0.395 |       | μC   |
| Internal gate resistor               | $R_{Gint}$    | $T_{vj} = 25\text{ °C}$                                                                      |                          |        | 0     |       | Ω    |
| Input capacitance                    | $C_{ies}$     | $f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$       |                          |        | 4.77  |       | nF   |
| Reverse transfer capacitance         | $C_{res}$     | $f = 100\text{ kHz}, T_{vj} = 25\text{ °C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$       |                          |        | 0.017 |       | nF   |
| Collector-emitter cut-off current    | $I_{CES}$     | $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}$                                                | $T_{vj} = 25\text{ °C}$  |        |       | 0.004 | mA   |
| Gate-emitter leakage current         | $I_{GES}$     | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25\text{ °C}$                           |                          |        |       | 100   | nA   |
| Turn-on delay time (inductive load)  | $t_{don}$     | $I_C = 25\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 9.1\text{ Ω}$ | $T_{vj} = 25\text{ °C}$  |        | 0.041 |       | μs   |
|                                      |               |                                                                                              | $T_{vj} = 125\text{ °C}$ |        | 0.043 |       |      |
|                                      |               |                                                                                              | $T_{vj} = 175\text{ °C}$ |        | 0.044 |       |      |
| Rise time (inductive load)           | $t_r$         | $I_C = 25\text{ A}, V_{CE} = 600\text{ V}, V_{GE} = \pm 15\text{ V}, R_{Gon} = 9.1\text{ Ω}$ | $T_{vj} = 25\text{ °C}$  |        | 0.023 |       | μs   |
|                                      |               |                                                                                              | $T_{vj} = 125\text{ °C}$ |        | 0.027 |       |      |
|                                      |               |                                                                                              | $T_{vj} = 175\text{ °C}$ |        | 0.029 |       |      |

**Table 10** Characteristic values (continued)

| Parameter                               | Symbol             | Note or test condition                                                                                                                                                                                                                                  | Values                                                                     |       |       | Unit             |
|-----------------------------------------|--------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------|-------|-------|------------------|
|                                         |                    |                                                                                                                                                                                                                                                         | Min.                                                                       | Typ.  | Max.  |                  |
| Turn-off delay time<br>(inductive load) | $t_{\text{doff}}$  | $I_C = 25 \text{ A}$ , $V_{\text{CE}} = 600 \text{ V}$ ,<br>$V_{\text{GE}} = \pm 15 \text{ V}$ , $R_{\text{Goff}} = 9.1 \Omega$                                                                                                                         | $T_{\text{vj}} = 25 \text{ }^\circ\text{C}$                                | 0.250 |       | $\mu\text{s}$    |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 125 \text{ }^\circ\text{C}$                               | 0.330 |       |                  |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 175 \text{ }^\circ\text{C}$                               | 0.360 |       |                  |
| Fall time (inductive load)              | $t_f$              | $I_C = 25 \text{ A}$ , $V_{\text{CE}} = 600 \text{ V}$ ,<br>$V_{\text{GE}} = \pm 15 \text{ V}$ , $R_{\text{Goff}} = 9.1 \Omega$                                                                                                                         | $T_{\text{vj}} = 25 \text{ }^\circ\text{C}$                                | 0.120 |       | $\mu\text{s}$    |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 125 \text{ }^\circ\text{C}$                               | 0.210 |       |                  |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 175 \text{ }^\circ\text{C}$                               | 0.270 |       |                  |
| Turn-on energy loss per pulse           | $E_{\text{on}}$    | $I_C = 25 \text{ A}$ , $V_{\text{CE}} = 600 \text{ V}$ ,<br>$L_\sigma = 35 \text{ nH}$ , $V_{\text{GE}} = \pm 15 \text{ V}$ ,<br>$R_{\text{Gon}} = 9.1 \Omega$ , $di/dt = 795 \text{ A}/\mu\text{s}$ ( $T_{\text{vj}} = 175 \text{ }^\circ\text{C}$ )   | $T_{\text{vj}} = 25 \text{ }^\circ\text{C}$                                | 1.19  |       | mJ               |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 125 \text{ }^\circ\text{C}$                               | 1.56  |       |                  |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 175 \text{ }^\circ\text{C}$                               | 1.75  |       |                  |
| Turn-off energy loss per pulse          | $E_{\text{off}}$   | $I_C = 25 \text{ A}$ , $V_{\text{CE}} = 600 \text{ V}$ ,<br>$L_\sigma = 35 \text{ nH}$ , $V_{\text{GE}} = \pm 15 \text{ V}$ ,<br>$R_{\text{Goff}} = 9.1 \Omega$ , $dv/dt = 3020 \text{ V}/\mu\text{s}$ ( $T_{\text{vj}} = 175 \text{ }^\circ\text{C}$ ) | $T_{\text{vj}} = 25 \text{ }^\circ\text{C}$                                | 1.62  |       | mJ               |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 125 \text{ }^\circ\text{C}$                               | 2.59  |       |                  |
|                                         |                    |                                                                                                                                                                                                                                                         | $T_{\text{vj}} = 175 \text{ }^\circ\text{C}$                               | 3.2   |       |                  |
| SC data                                 | $I_{\text{SC}}$    | $V_{\text{GE}} \leq 15 \text{ V}$ , $V_{\text{CC}} = 800 \text{ V}$ ,<br>$V_{\text{CEmax}} = V_{\text{CES}} - L_{\text{sCE}} \cdot di/dt$                                                                                                               | $t_P \leq 8 \mu\text{s}$ ,<br>$T_{\text{vj}} = 150 \text{ }^\circ\text{C}$ | 80    |       | A                |
|                                         |                    |                                                                                                                                                                                                                                                         | $t_P \leq 7 \mu\text{s}$ ,<br>$T_{\text{vj}} = 175 \text{ }^\circ\text{C}$ | 75    |       |                  |
| Thermal resistance, junction to case    | $R_{\text{thJC}}$  | per IGBT                                                                                                                                                                                                                                                |                                                                            |       | 0.967 | K/W              |
| Thermal resistance, case to heatsink    | $R_{\text{thCH}}$  | per IGBT, $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}^2\text{K})$                                                                                                                                                                                  |                                                                            | 0.171 |       | K/W              |
| Temperature under switching conditions  | $T_{\text{vj op}}$ |                                                                                                                                                                                                                                                         | -40                                                                        |       | 175   | $^\circ\text{C}$ |

Note:  $T_{\text{vj op}} > 150^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 6 Diode, Chopper

**Table 11** Maximum rated values

| Parameter                       | Symbol           | Note or test condition                      | Values | Unit |
|---------------------------------|------------------|---------------------------------------------|--------|------|
| Repetitive peak reverse voltage | $V_{\text{RRM}}$ | $T_{\text{vj}} = 25 \text{ }^\circ\text{C}$ | 1200   | V    |
| Continuous DC forward current   | $I_F$            |                                             | 10     | A    |
| Repetitive peak forward current | $I_{\text{FRM}}$ | $t_P = 1 \text{ ms}$                        | 20     | A    |

**Table 11** Maximum rated values (continued)

| Parameter      | Symbol | Note or test condition                      | Values                       | Unit                 |
|----------------|--------|---------------------------------------------|------------------------------|----------------------|
| $I^2t$ - value | $I^2t$ | $t_p = 10 \text{ ms}$ , $V_R = 0 \text{ V}$ | $T_{vj} = 125^\circ\text{C}$ | $\text{A}^2\text{s}$ |
|                |        |                                             | $T_{vj} = 175^\circ\text{C}$ |                      |

**Table 12** Characteristic values

| Parameter                              | Symbol             | Note or test condition                                                                                                                               | Values                       |       |      | Unit             |
|----------------------------------------|--------------------|------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------|-------|------|------------------|
|                                        |                    |                                                                                                                                                      | Min.                         | Typ.  | Max. |                  |
| Forward voltage                        | $V_F$              | $I_F = 10 \text{ A}$ , $V_{GE} = 0 \text{ V}$                                                                                                        | $T_{vj} = 25^\circ\text{C}$  | 1.72  | TBD  | V                |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 125^\circ\text{C}$ | 1.59  |      |                  |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 175^\circ\text{C}$ | 1.52  |      |                  |
| Peak reverse recovery current          | $I_{RM}$           | $V_R = 600 \text{ V}$ , $I_F = 10 \text{ A}$ ,<br>$V_{GE} = -15 \text{ V}$ , $-di_F/dt = 250 \text{ A}/\mu\text{s}$ ( $T_{vj} = 175^\circ\text{C}$ ) | $T_{vj} = 25^\circ\text{C}$  | 10    |      | A                |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 125^\circ\text{C}$ | 14    |      |                  |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 175^\circ\text{C}$ | 17    |      |                  |
| Recovered charge                       | $Q_r$              | $V_R = 600 \text{ V}$ , $I_F = 10 \text{ A}$ ,<br>$V_{GE} = -15 \text{ V}$ , $-di_F/dt = 250 \text{ A}/\mu\text{s}$ ( $T_{vj} = 175^\circ\text{C}$ ) | $T_{vj} = 25^\circ\text{C}$  | 0.95  |      | $\mu\text{C}$    |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 125^\circ\text{C}$ | 1.85  |      |                  |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 175^\circ\text{C}$ | 2.44  |      |                  |
| Reverse recovery energy                | $E_{rec}$          | $V_R = 600 \text{ V}$ , $I_F = 10 \text{ A}$ ,<br>$V_{GE} = -15 \text{ V}$ , $-di_F/dt = 250 \text{ A}/\mu\text{s}$ ( $T_{vj} = 175^\circ\text{C}$ ) | $T_{vj} = 25^\circ\text{C}$  | 0.39  |      | mJ               |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 125^\circ\text{C}$ | 0.83  |      |                  |
|                                        |                    |                                                                                                                                                      | $T_{vj} = 175^\circ\text{C}$ | 1.09  |      |                  |
| Thermal resistance, junction to case   | $R_{thJC}$         | per diode                                                                                                                                            |                              |       | 1.81 | K/W              |
| Thermal resistance, case to heatsink   | $R_{thCH}$         | per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}^2\text{K})$                                                                                     |                              | 0.181 |      | K/W              |
| Temperature under switching conditions | $T_{vj\text{ op}}$ |                                                                                                                                                      | -40                          |       | 175  | $^\circ\text{C}$ |

Note:  $T_{vj\text{ op}} > 150^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 7 NTC-Thermistor

**Table 13** Characteristic values

| Parameter              | Symbol       | Note or test condition                                 | Values |      |      | Unit       |
|------------------------|--------------|--------------------------------------------------------|--------|------|------|------------|
|                        |              |                                                        | Min.   | Typ. | Max. |            |
| Rated resistance       | $R_{25}$     | $T_{NTC} = 25^\circ\text{C}$                           |        | 5    |      | k $\Omega$ |
| Deviation of $R_{100}$ | $\Delta R/R$ | $T_{NTC} = 100^\circ\text{C}$ , $R_{100} = 493 \Omega$ | -5     |      | 5    | %          |
| Power dissipation      | $P_{25}$     | $T_{NTC} = 25^\circ\text{C}$                           |        |      | 20   | mW         |

**Table 13**                      **Characteristic values (continued)**

| Parameter | Symbol       | Note or test condition                                        | Values |      |      | Unit |
|-----------|--------------|---------------------------------------------------------------|--------|------|------|------|
|           |              |                                                               | Min.   | Typ. | Max. |      |
| B-value   | $B_{25/50}$  | $R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$  |        | 3375 |      | K    |
| B-value   | $B_{25/80}$  | $R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$  |        | 3411 |      | K    |
| B-value   | $B_{25/100}$ | $R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$ |        | 3433 |      | K    |

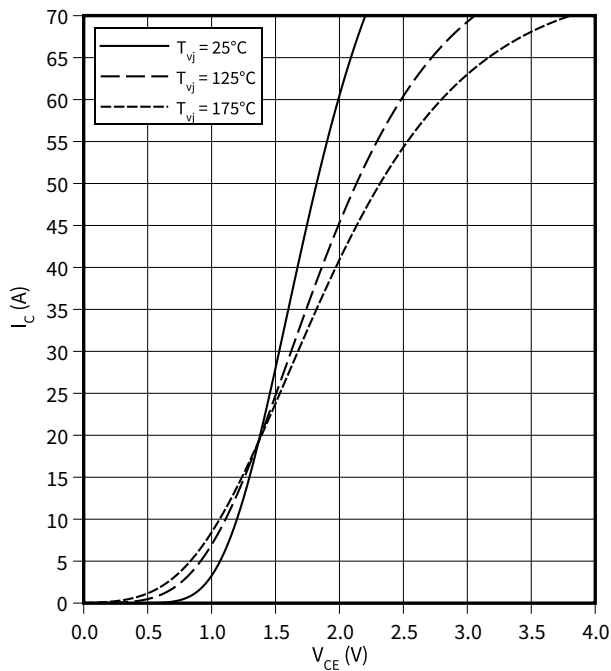
*Note:*                      *Specification according to the valid application note.*

8 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

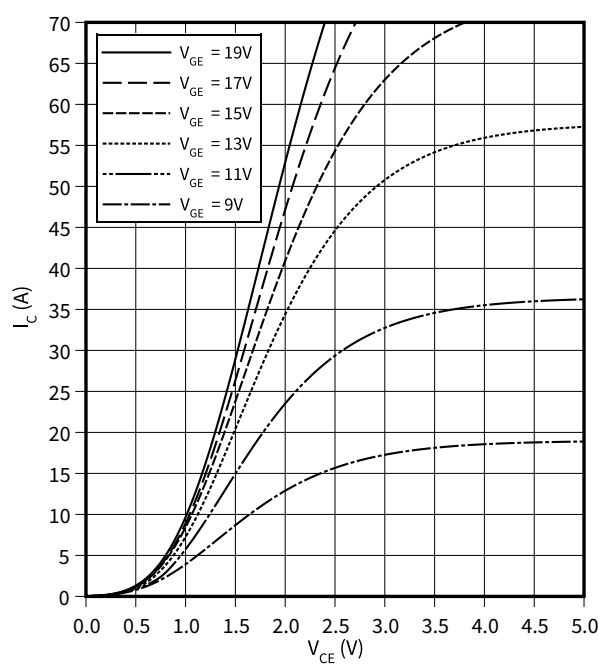
$V_{GE} = 15\text{ V}$



output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

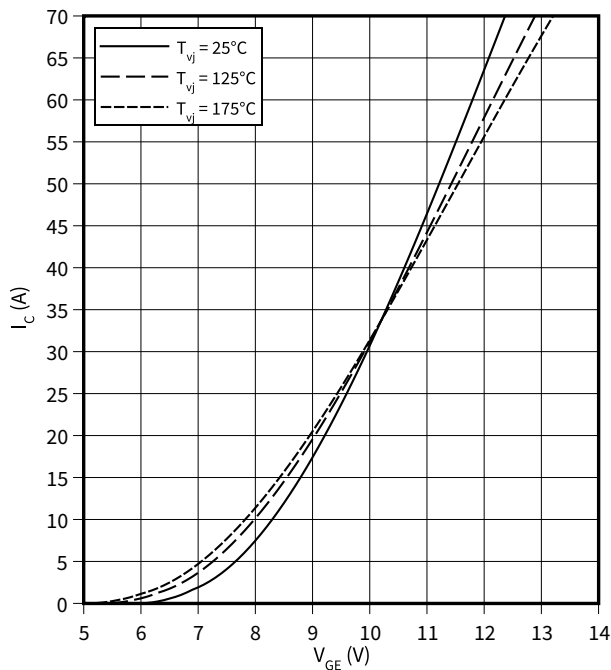
$T_{vj} = 175\text{ °C}$



transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

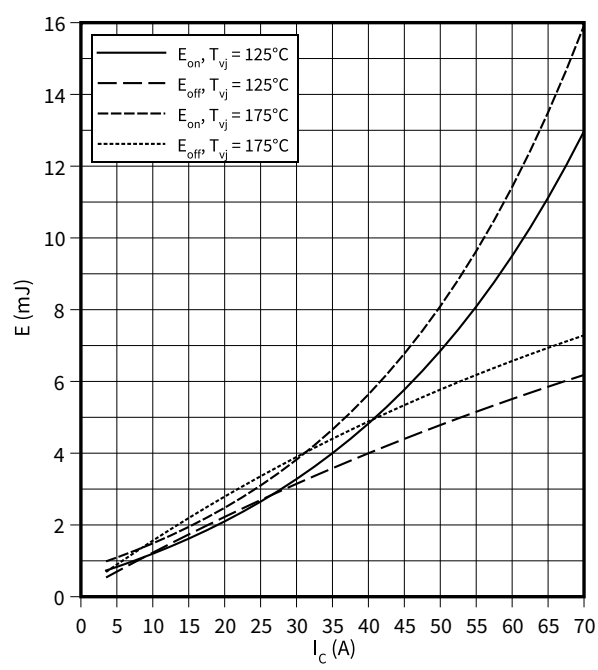
$V_{CE} = 20\text{ V}$



switching losses (typical), IGBT, Inverter

$E = f(I_C)$

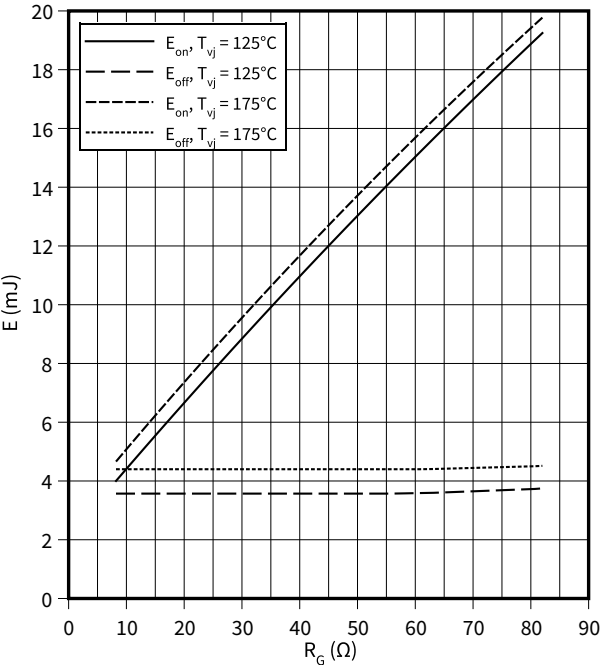
$R_{Goff} = 8.2\text{ }\Omega$ ,  $R_{Gon} = 8.2\text{ }\Omega$ ,  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$



8 Characteristics diagrams

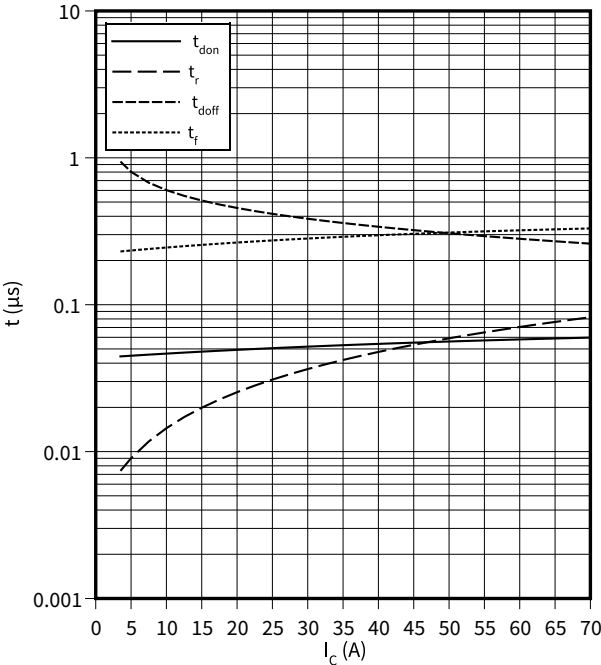
switching losses (typical), IGBT, Inverter

$E = f(R_G)$   
 $I_C = 35\text{ A}$ ,  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$



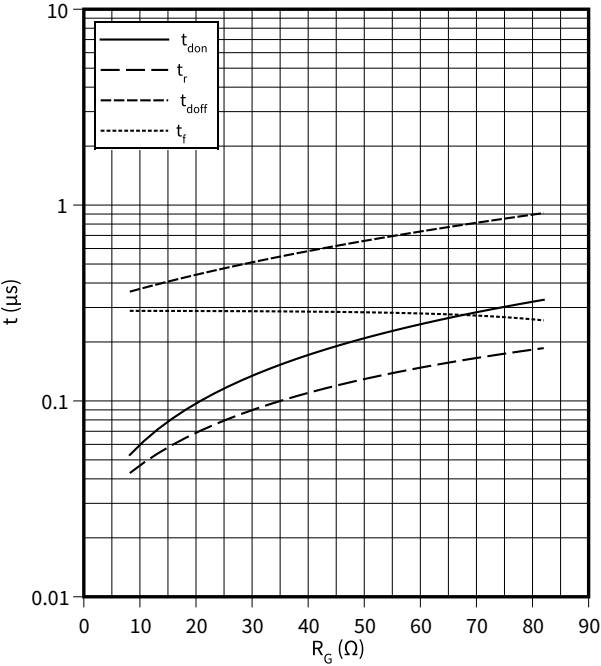
switching times (typical), IGBT, Inverter

$t = f(I_C)$   
 $R_{Goff} = 8.2\ \Omega$ ,  $R_{Gon} = 8.2\ \Omega$ ,  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $T_{vj} = 175\text{ °C}$



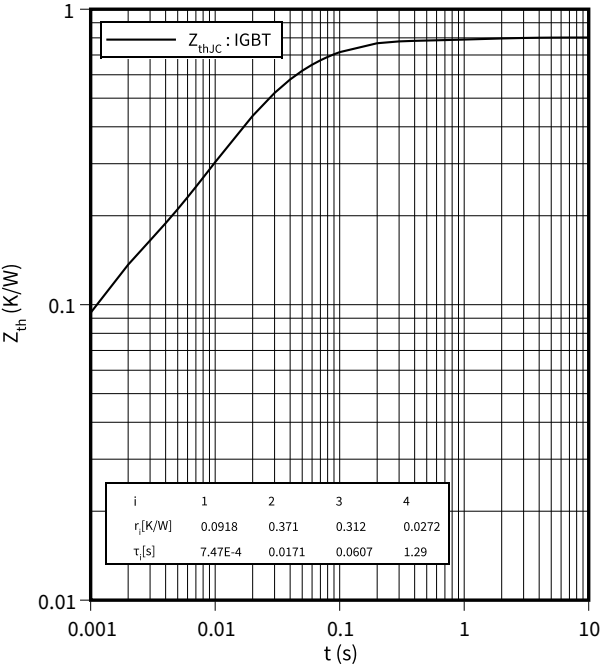
switching times (typical), IGBT, Inverter

$t = f(R_G)$   
 $I_C = 35\text{ A}$ ,  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $T_{vj} = 175\text{ °C}$



transient thermal impedance , IGBT, Inverter

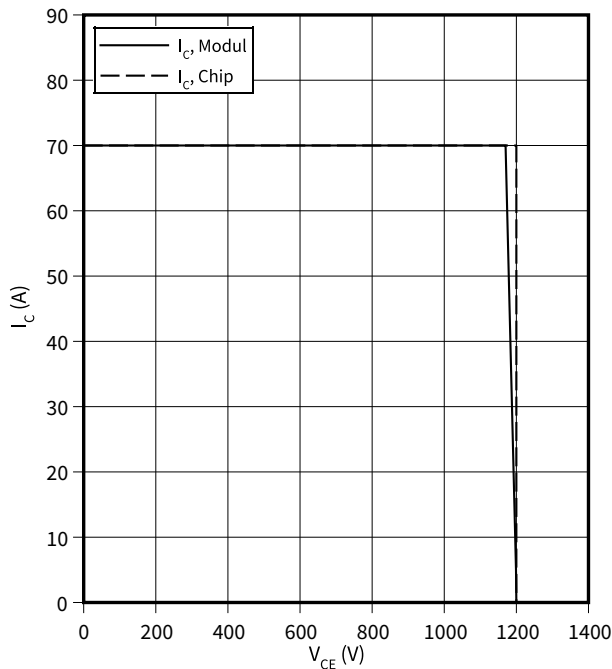
$Z_{th} = f(t)$



8 Characteristics diagrams

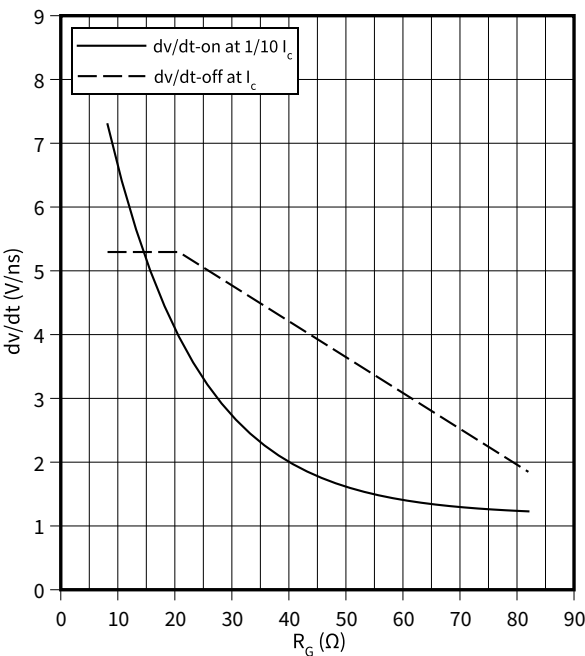
reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$   
 $R_{Goff} = 8.2 \Omega$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $T_{vj} = 175 \text{ }^\circ\text{C}$



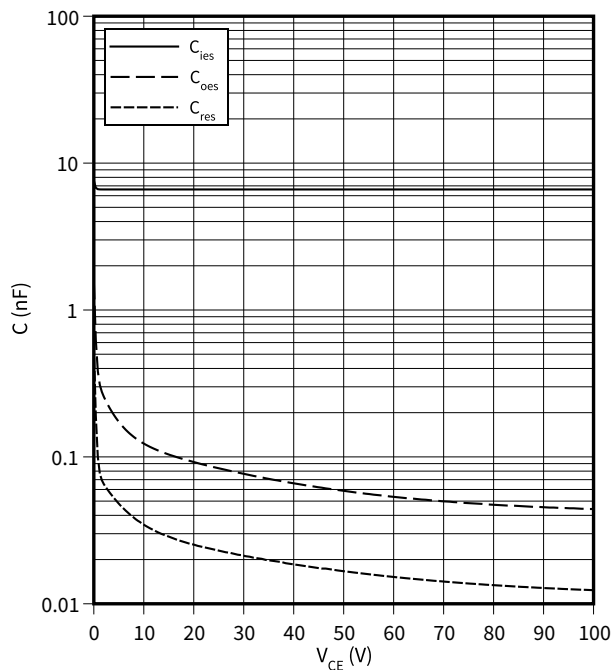
dv/dt (typical), IGBT, Inverter

$dv/dt = f(R_G)$   
 $I_C = 35 \text{ A}$ ,  $V_{CE} = 600 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $T_{vj} = 25 \text{ }^\circ\text{C}$



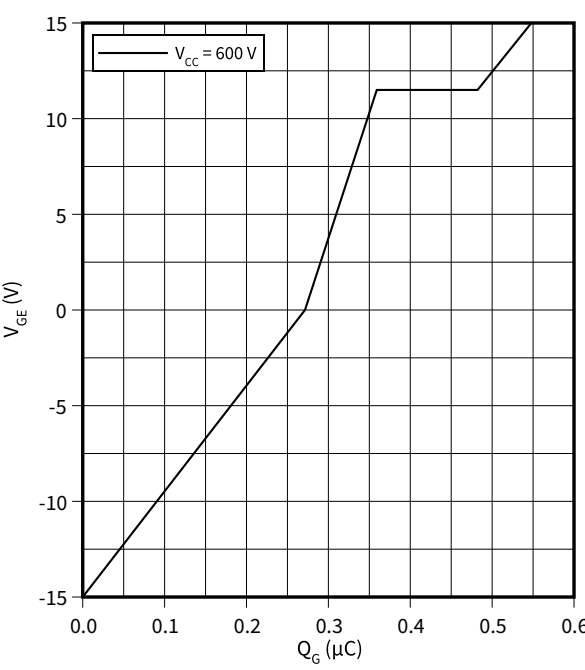
capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$   
 $f = 100 \text{ kHz}$ ,  $V_{GE} = 0 \text{ V}$ ,  $T_{vj} = 25 \text{ }^\circ\text{C}$



gate charge characteristic (typical), IGBT, Inverter

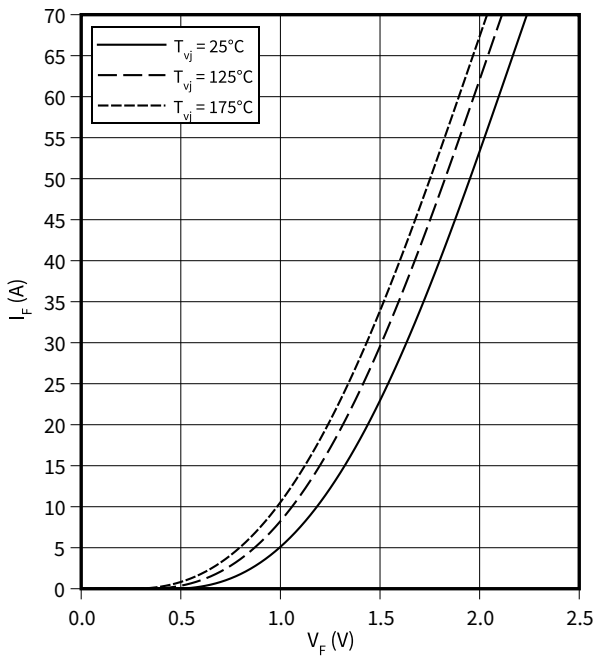
$V_{GE} = f(Q_G)$   
 $I_C = 35 \text{ A}$ ,  $T_{vj} = 25 \text{ }^\circ\text{C}$



8 Characteristics diagrams

forward characteristic (typical), Diode, Inverter

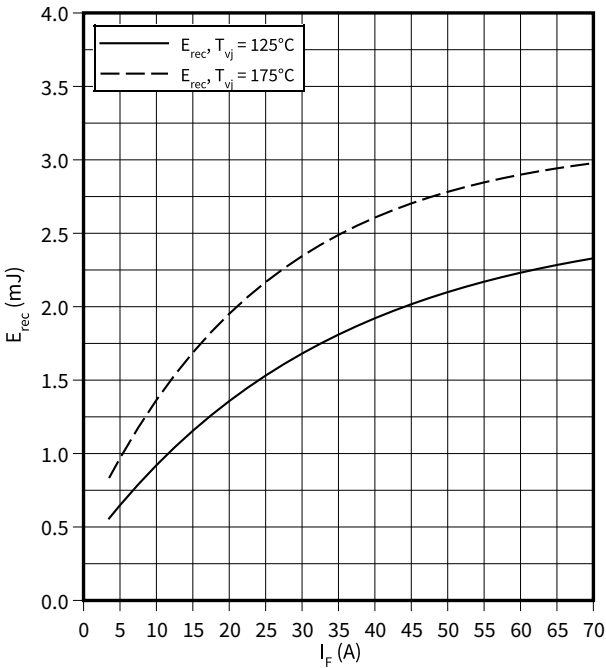
$I_F = f(V_F)$



switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

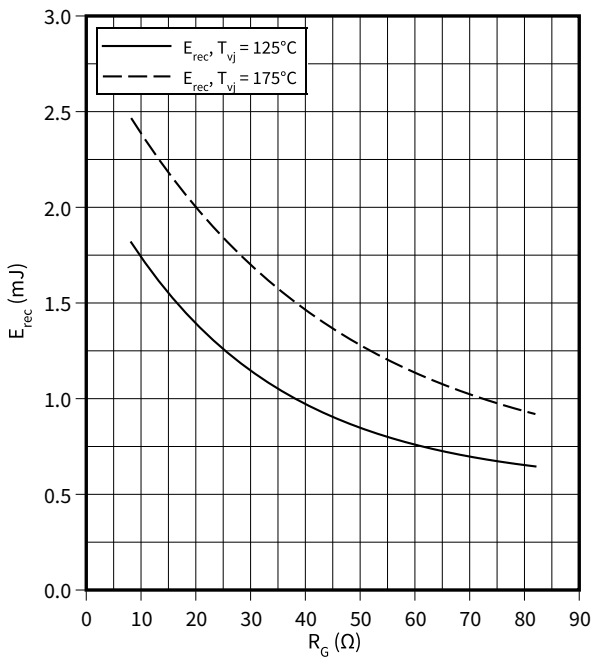
$R_{Gon} = 8.2\ \Omega, V_{CE} = 600\ \text{V}$



switching losses (typical), Diode, Inverter

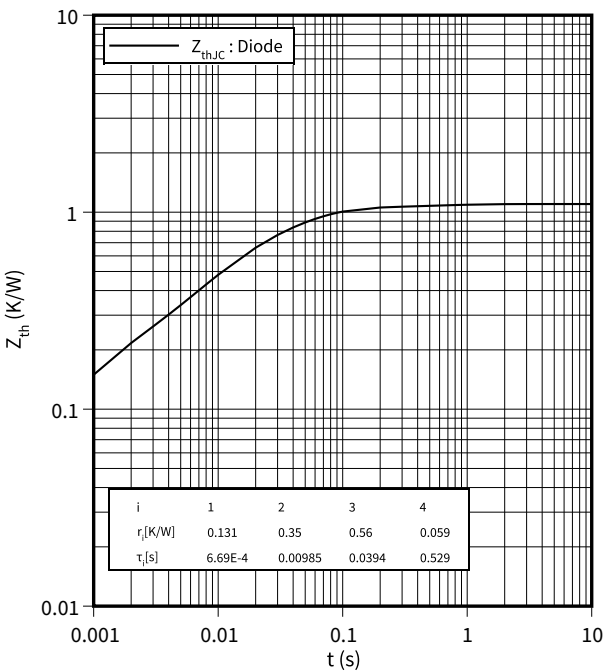
$E_{rec} = f(R_G)$

$V_{CE} = 600\ \text{V}, I_F = 35\ \text{A}$



transient thermal impedance , Diode, Inverter

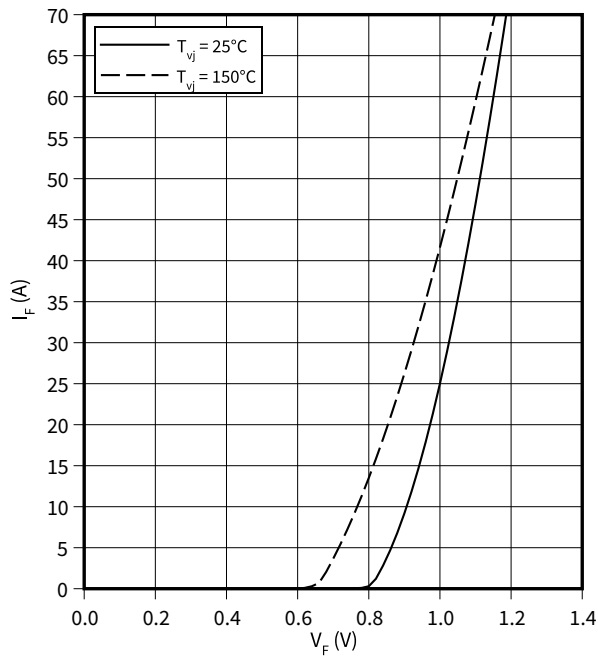
$Z_{th} = f(t)$



8 Characteristics diagrams

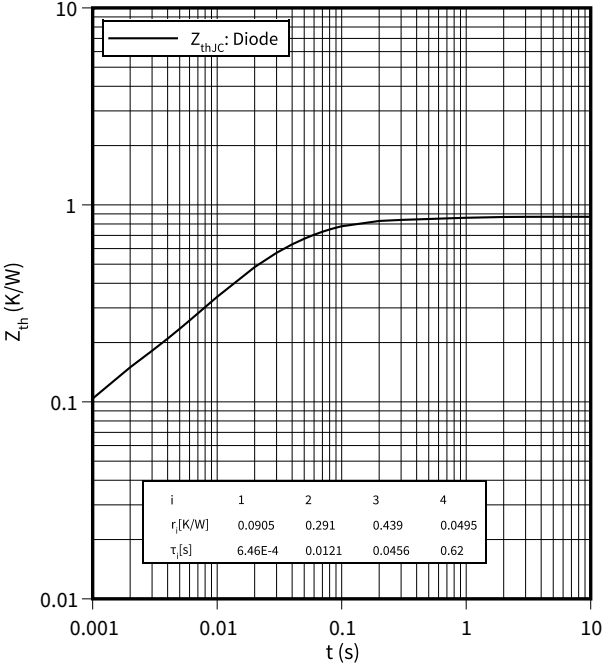
forward characteristic (typical), Diode, Rectifier

$I_F = f(V_F)$



transient thermal impedance , Diode, Rectifier

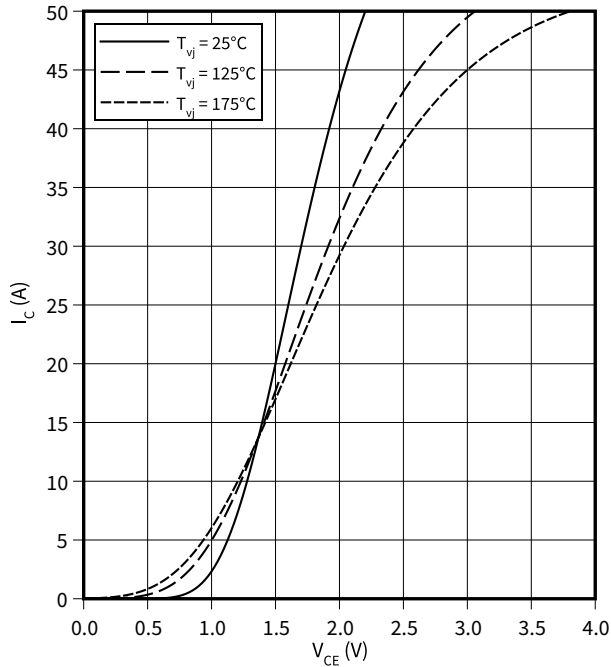
$Z_{th} = f(t)$



output characteristic (typical), IGBT-Chopper

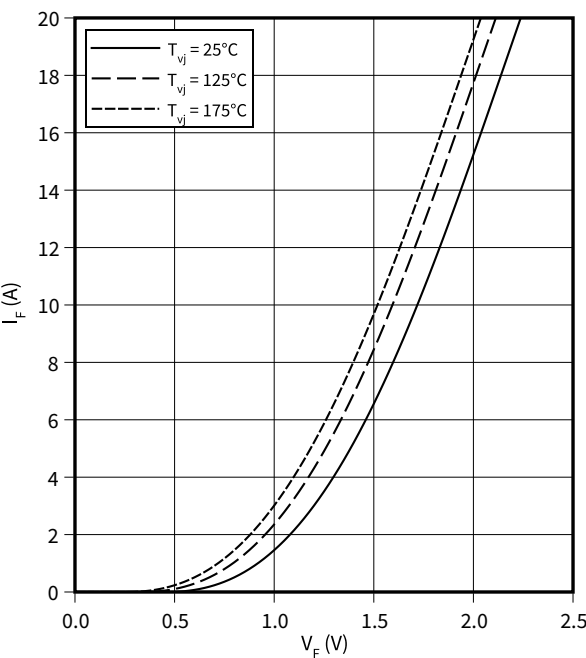
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



forward characteristic (typical), Diode, Chopper

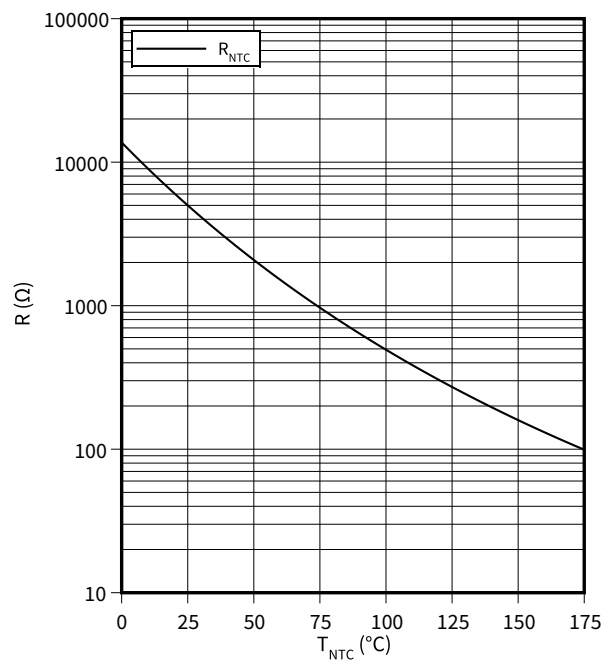
$I_F = f(V_F)$



8 Characteristics diagrams

temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 Circuit diagram

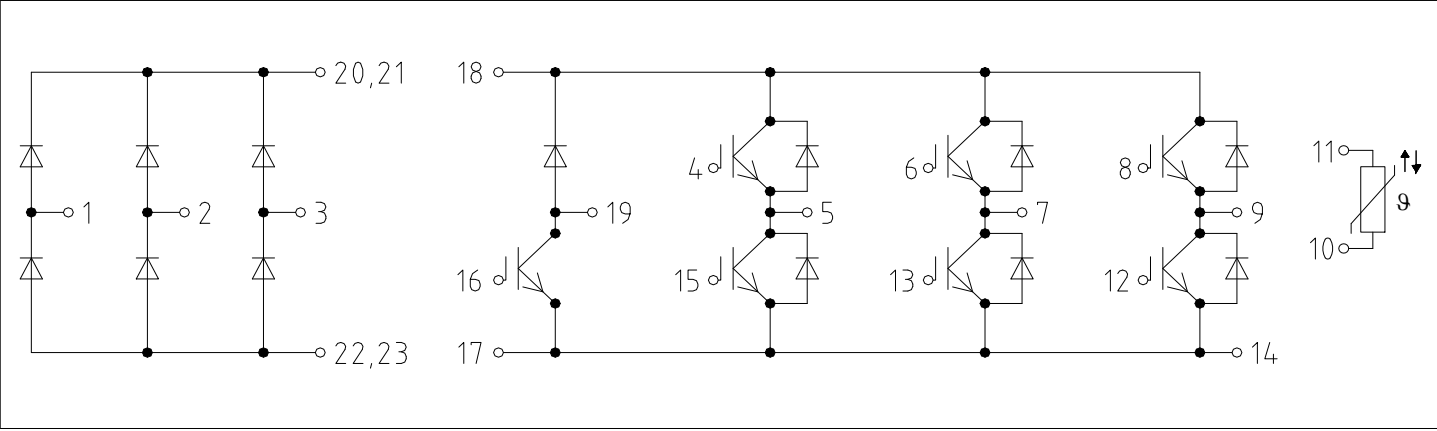
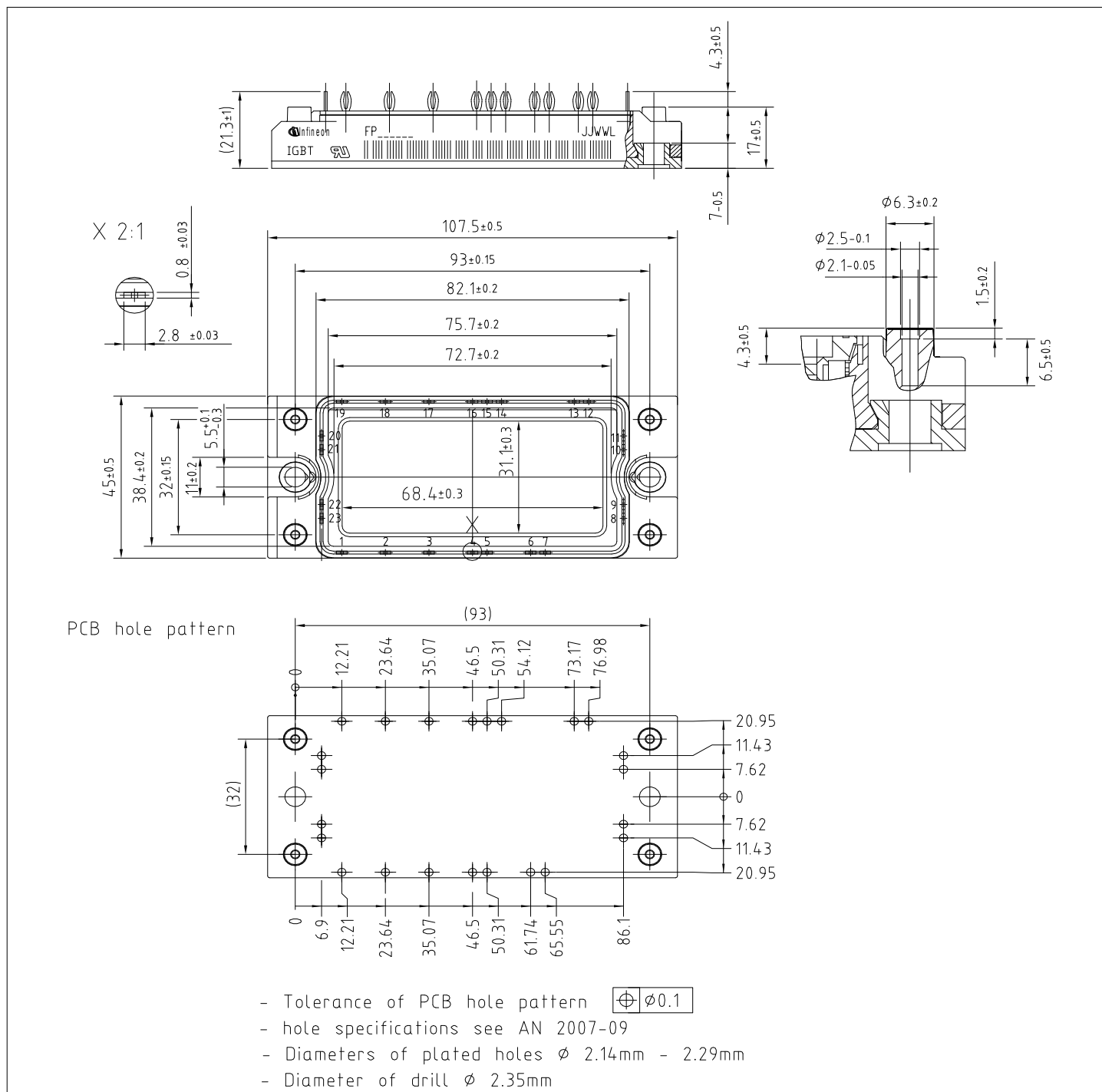


Figure 2

## 10 Package outlines



**Figure 3**

### Figure 4

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Revision history

## Revision history

| Document revision | Date of release | Description of changes |
|-------------------|-----------------|------------------------|
| 0.10              | 2021-06-17      | Initial version        |

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